

MOSFET Maximum Ratings T₁ = 25°C unless otherwise noted.

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-to-Source Voltage		40	V	
V _{GS}	Gate-to-Source Voltage		±20	V	
I _D	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C =25°C	300	•	
	Pulsed Drain Current	T _C = 25°C	See Figure 4	— A	
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	1064	mJ	
P _D	Power Dissipation		429	W	
	Derate Above 25°C		2.86	W/ ^o C	
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 175	°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.35	°C/W	
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	43	°C/W	

Notes:

1: Current is limited by bondwire configuration.

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Starting T_J = 25°C, L = 0.3mH, I_{AS} = 84A, V_{DD} = 40V during inductor charging and V_{DD} = 0V during time in avalanche.
R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design, while R_{0JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

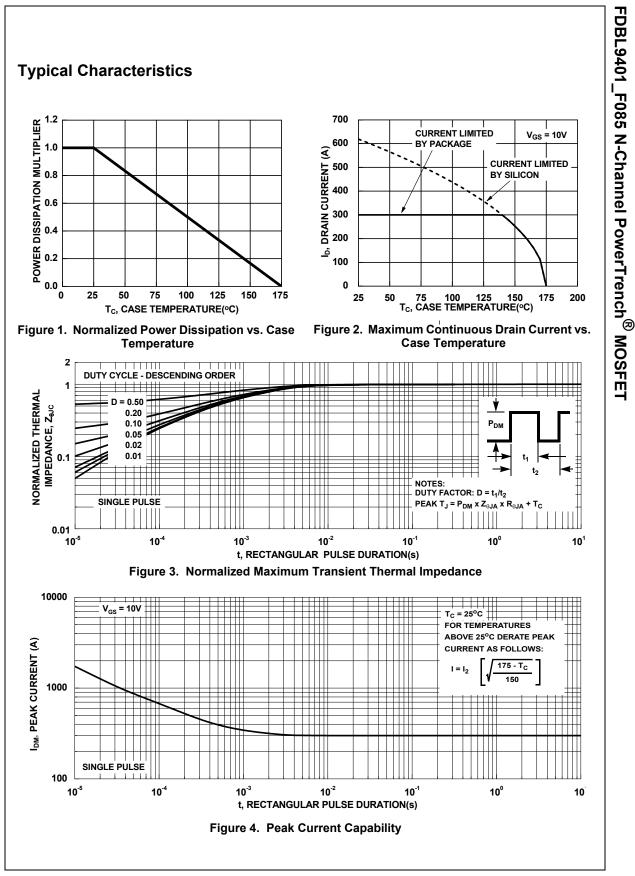
Package Marking and Ordering Information

Device Marking	Device	Package			
FDBL9401	FDBL9401_F085	MO-299A	-	-	-

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
-	racteristics						
B _{VDSS}	Drain-to-Source Breakdown Voltage	I _D = 250μA, \	/ _{GS} = 0V	40	-	-	V
	Drain-to-Source Leakage Current	V _{DS} =40V,		-	-	1	μA
IDSS			$T_{\rm J} = 175^{\rm o}C$ (Note 4)	-	-	1	mA
I _{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$	· · · ·	-	-	±100	nA
On Cha	racteristics			_			
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{I}$	_D = 250μA	2.0	3.0	4.0	V
R _{DS(on)}	Drain to Source On Resistance		T _J = 25 ^o C	-	0.50	0.65	mΩ
DS(on)	Drain to Source On Resistance	V _{GS} = 10V	T _J = 175 ^o C (Note 4)	-	0.86	1.10	mΩ
C _{iss}	c Characteristics	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		-	15900	-	pF
C _{oss}	Output Capacitance			-	4025	-	pF
C _{rss}	Reverse Transfer Capacitance			-	604	-	pF
R _g	Gate Resistance	f = 1MHz		-	2.6	-	Ω
⊇ _{g(ToT)}	Total Gate Charge at 10V	V _{GS} = 0 to 10	0V V _{DD} = 20V	-	220	296	nC
$Q_{g(th)}$	Threshold Gate Charge	V _{GS} = 0 to 2\		-	29	39	nC
Q _{gs}	Gate to Source Gate Charge			-	73	-	nC
ୁ _{gd}	Gate to Drain "Miller" Charge			-	41	-	nC
	ng Characteristics		Ι				1
on	Turn-On Time		-	-	-	221	ns
d(on)	Turn-On Delay Rise Time	$\begin{array}{c c} & - & 54 \\ \hline V_{DD} = 20V, I_D = 80A, & - & 82 \\ V_{GS} = 10V, R_{GEN} = 6\Omega & - & 106 \\ \hline & - & 52 \\ \hline & - & - & - \end{array}$				-	ns
r						-	ns
d(off)	Turn-Off Delay Fall Time			-	ns		
f ·	Turn-Off Time				-	- 215	ns ns
off				-	-	210	115
Drain-S	ource Diode Characteristics						T
V _{SD}	Source to Drain Diode Voltage	I _{SD} =80A, V _C		-	-	1.25	V
		I _{SD} = 40A, V		-	-	1.2	V
t _{rr}	Reverse Recovery Time		_{SD} /dt = 100A/µs,	-	119	133	ns
Q _{rr}	Reverse Recovery Charge	V _{DD} =32V		-	228	274	nC

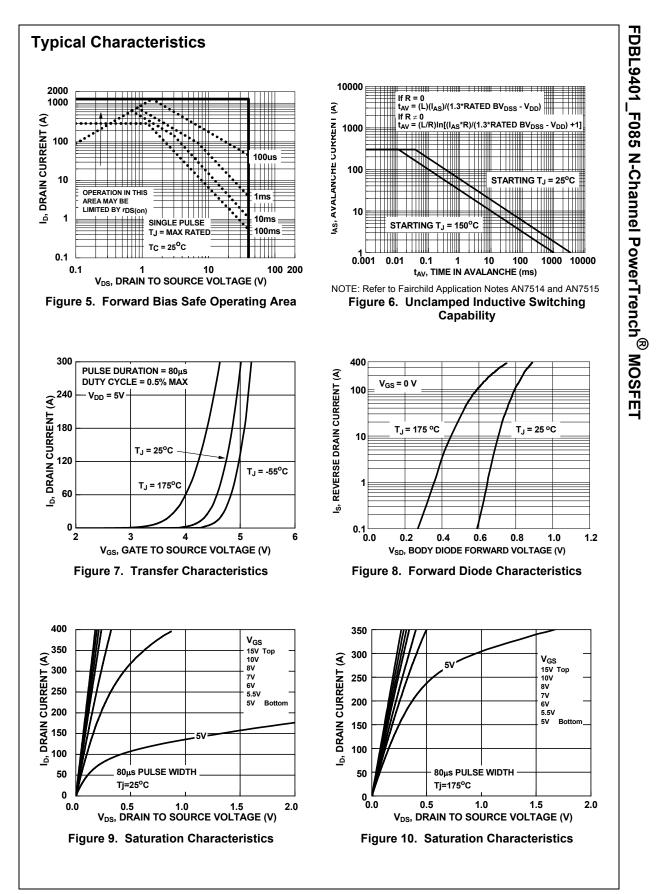
Note:

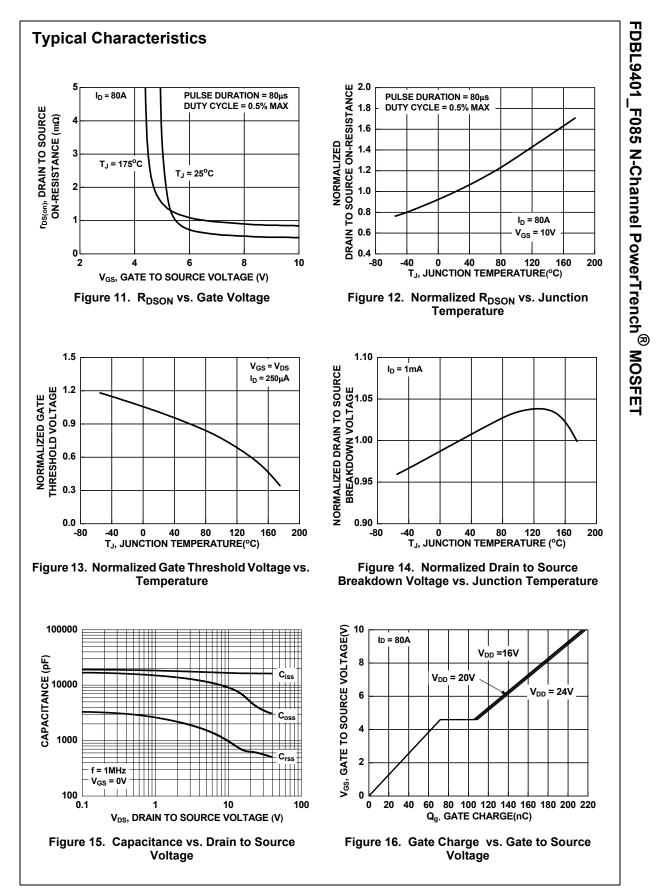
4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.



FDBL9401_F085 Rev. C2

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